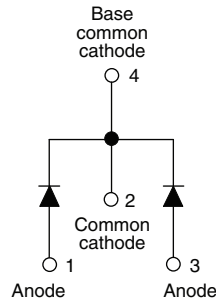


Ultrafast Rectifier, 2 x 3 A FRED Pt®



D-PAK (TO-252AA)



FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Compliant to RoHS Directive 2002/95/EC
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



RoHS
COMPLIANT

DESCRIPTION/APPLICATIONS

Vishay Semiconductors' 200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

PRODUCT SUMMARY

Package	D-PAK (TO-252AA)
$I_{F(AV)}$	2 x 3 A
V_R	200 V
V_F at I_F	1.0 V
t_{rr} typ.	See Recovery table
T_J max.	175 °C
Diode variation	Common cathode

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V_{RRM}		200	V
Average rectified forward current per device	$I_{F(AV)}$	Total device, rated V_R , $T_C = 159$ °C	6	A
Non-repetitive peak surge current	I_{FSM}		50	
Peak repetitive forward current per diode	I_{FM}	Rated V_R , square wave, 20 kHz, $T_C = 159$ °C	6	
Operating junction and storage temperatures	T_J, T_{Stg}		- 65 to 175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100$ μ A	200	-	-	V
Forward voltage	V_F	$I_F = 3$ A	-	-	1	
		$I_F = 3$ A, $T_J = 125$ °C	-	-	0.9	
		$I_F = 6$ A	-	-	1.2	
Reverse leakage current	I_R	$V_R = V_R$ rated	-	-	5	μ A
		$T_J = 125$ °C, $V_R = V_R$ rated	-	-	100	
Junction capacitance	C_T	$V_R = 200$ V	-	12	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

VS-6CWH02FNPbF



Vishay Semiconductors Ultrafast Rectifier, 2 x 3 A FRED Pt®

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time	t _{rr}	I _F = 1.0 A, di _F /dt = 50 A/μs, V _R = 30 V	-	-	35	ns	
		T _J = 25 °C	-	19	-		
		T _J = 125 °C	-	26	-		
Peak recovery current	I _{RRM}	I _F = 3 A V _R = 160 V di _F /dt = 200 A/μs	T _J = 25 °C	-	3.1	-	A
			T _J = 125 °C	-	4.6	-	
Reverse recovery charge	Q _{rr}		T _J = 25 °C	-	30	-	nC
			T _J = 125 °C	-	60	-	

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}	- 65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}	-	-	5	°C/W
Thermal resistance, junction to ambient per leg	R _{thJA}	-	-	80	
Thermal resistance, case to heatsink	R _{thCS}	-	-	-	
Weight		-	0.3	-	g
		-	0.01	-	oz.
Mounting torque		6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D-PAK		6CWH02FN	



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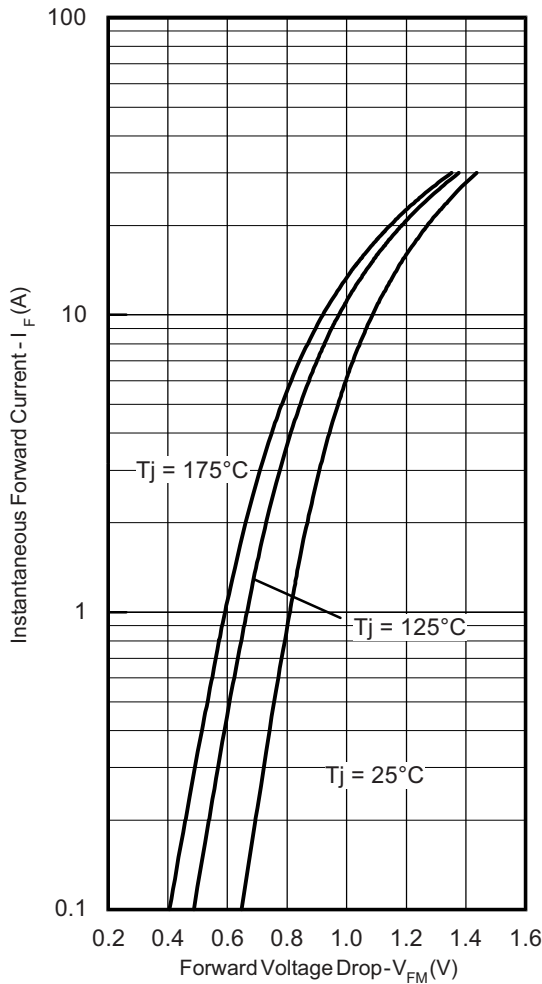


Fig. 1 - Maximum Forward Voltage Drop Characteristics

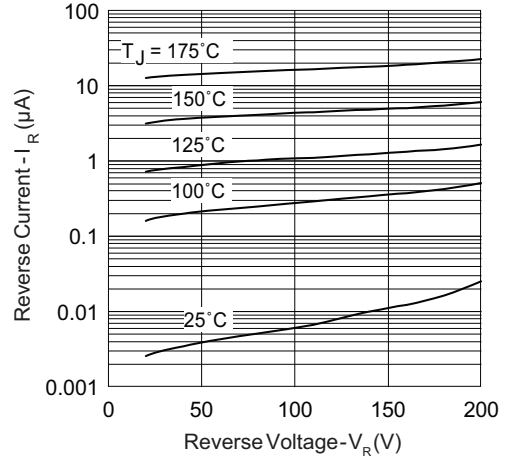


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

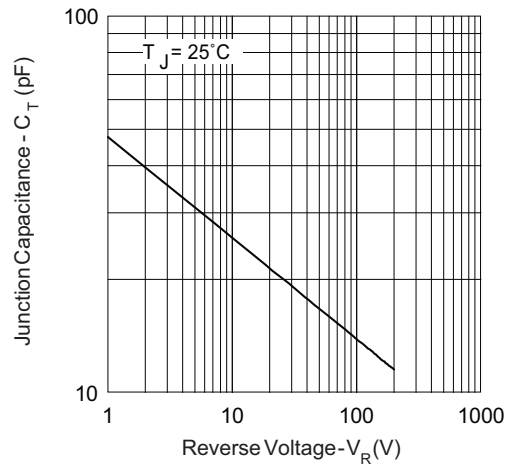


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

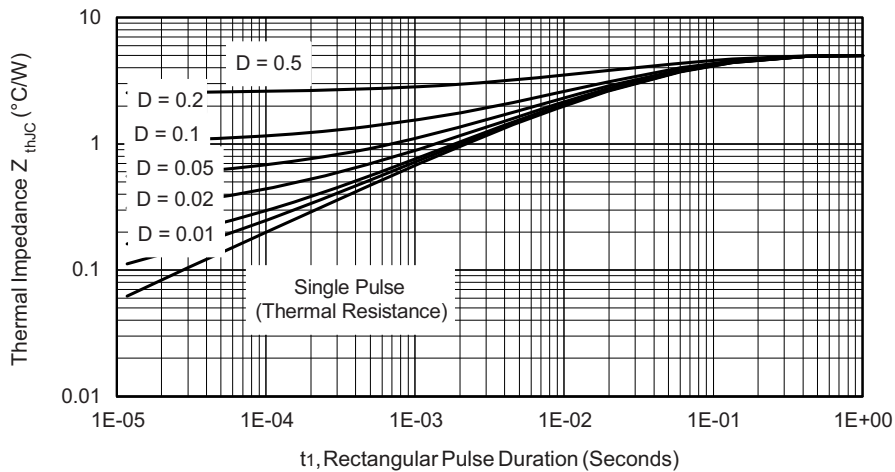


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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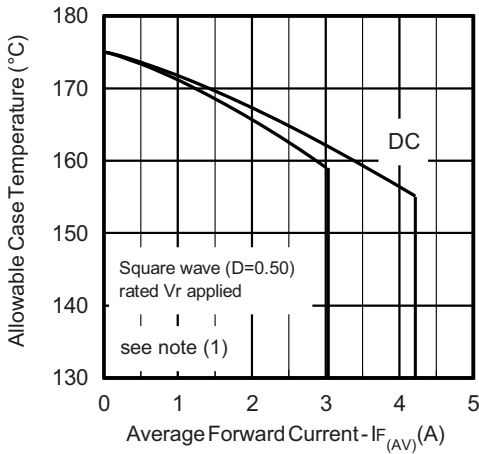


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

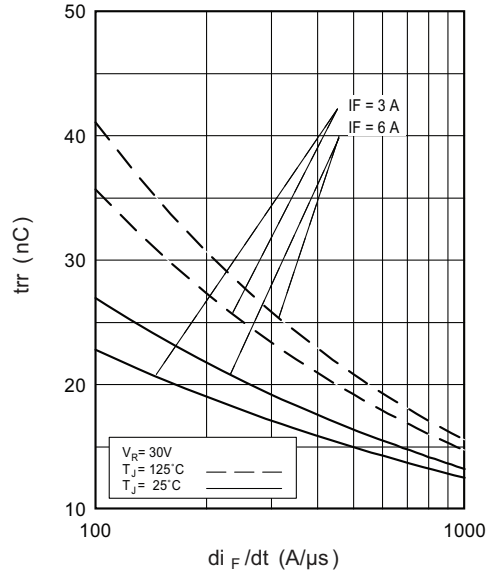


Fig. 7 - Typical Reverse Recovery vs. di_F/dt

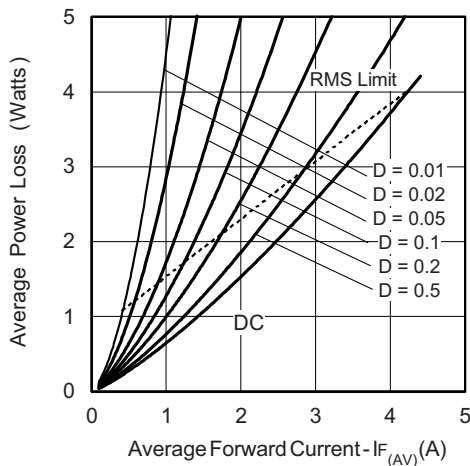


Fig. 6 - Forward Power Loss Characteristics

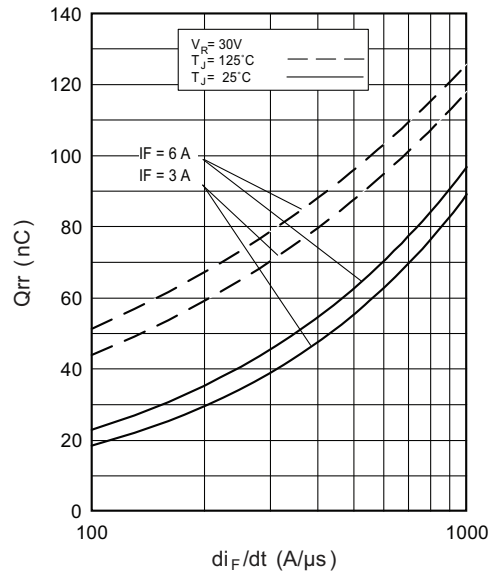


Fig. 8 - Typical Stored Charge vs. di_F/dt

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R

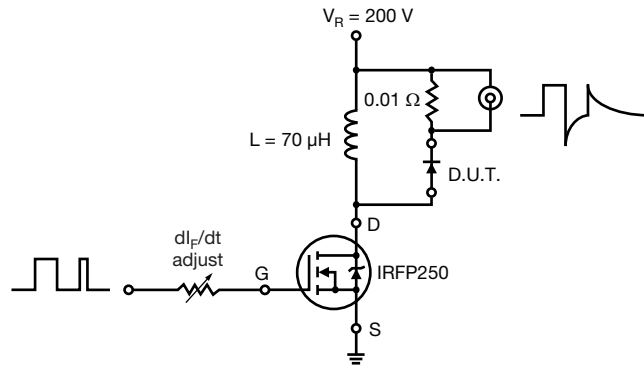
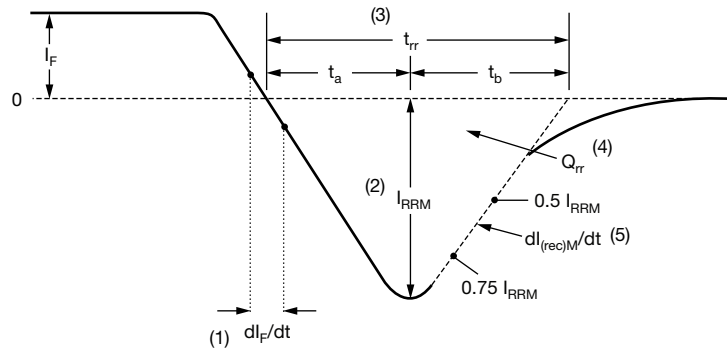


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt - rate of change of current through zero crossing
- (2) I_{RRM} - peak reverse recovery current
- (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}
- (5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

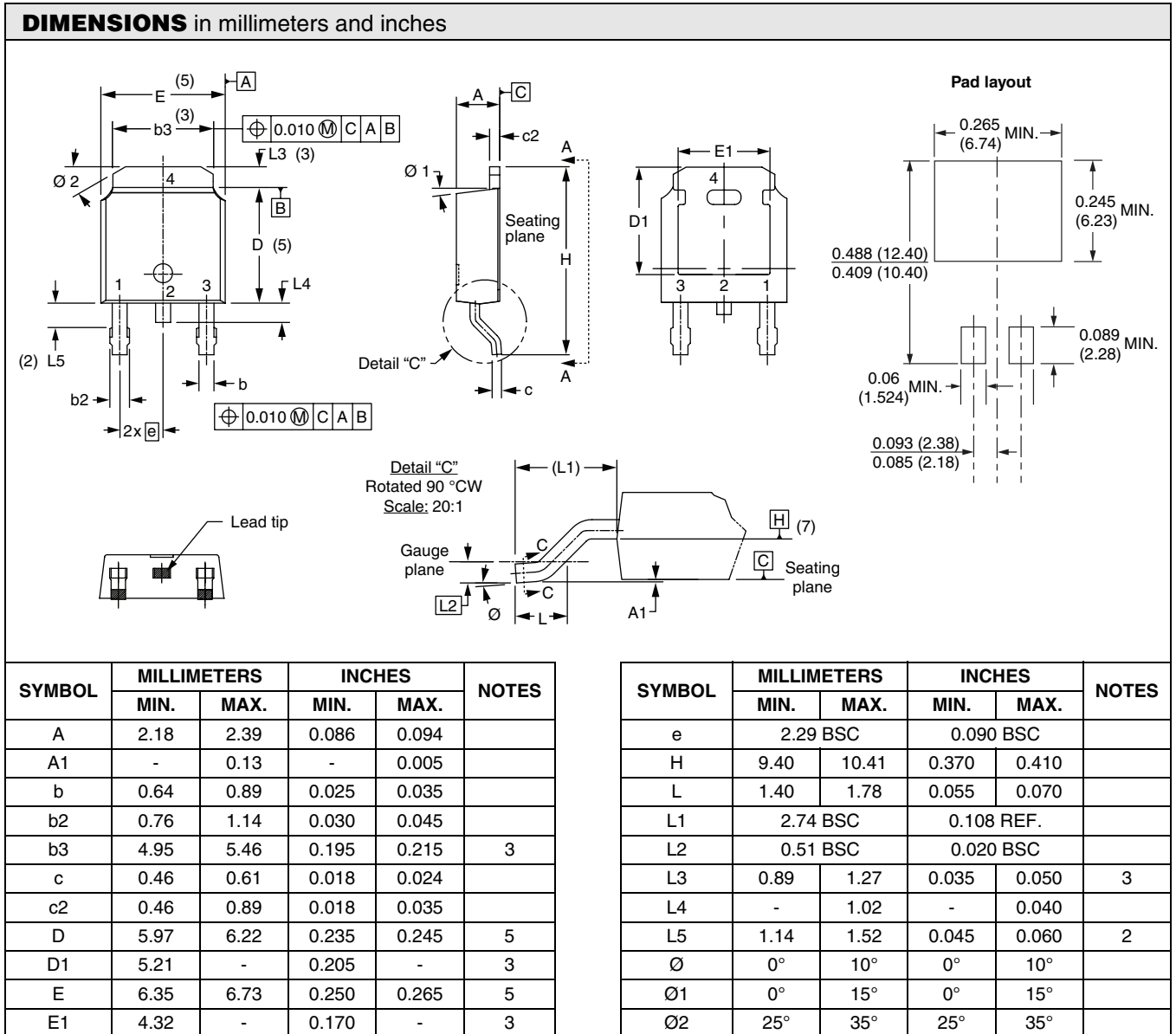
Device code	VS-	6	C	W	H	02	FN	TRL	PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Current rating (6 = 6 A)
- 3** - Center tap configuration
- 4** - Package identifier:
W = D-PAK
- 5** - H = Hyperfast recovery
- 6** - Voltage rating (02 = 200 V)
- 7** - FN = TO-252AA
- 8** -
 - None = Tube (50 pieces)
 - TR = Tape and reel
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)
- 9** - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95016
Part marking information	www.vishay.com/doc?95059
Packaging information	www.vishay.com/doc?95033



D-PAK (TO-252AA)



Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension uncontrolled in L5
- (3) Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- (4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- (5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (6) Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- (8) Outline conforms to JEDEC outline TO-252AA



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